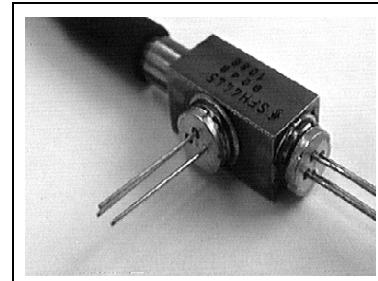


**BIDI™ Transceiver Optical Module for ATM-PON ONU Applications,  
1300 nm Emitting-/1550 nm Receiving Function, High Power FP-Laser,  
InGaAs/InP-PIN Photodiode with 622 Mbit/s Transimpedance Amplifier**

- Designed for applications in passive-optical networks according FSAN, ITU-G.983
- **Suitable for ONU applications, 622 Mbit/s downstream bitrate, Class B**
- Uncooled 1300 nm FPLaser Diode with Multi-Quantum Well structure
- Ternary Moniordiode at rear laser mirror for monitoring and control of radiant power
- Integrated Wavelength Division Multiplexer
- InGaAs/InP-PIN-photodiode with 1300 nm blocking filter and integrated 622 Mbit/s transimpedance amplifier
- Hermetically sealed subcomponents, similar to TO 18
- With singlemode fiber pigtail



### Maximum Ratings

Output power ratings refer to the optical port. The operating temperature of the submount is identical to the case temperature

Module	Symbol	Value	Unit
Operating temperature range at case	$T_C$	– 40 ... + 85	°C
Storage temperature range	$T_{stg}$	– 40 ... + 85	°C
Soldering temperature $t_{max} = 10$ s, 2 mm distance from bottom edge of case	$T_S$	260	°C

Laser Diode	Symbol	Value	Unit
Direct forward current	$I_F \text{ max}$	120	mA
Radiant power CW	$P_{opt \text{ max}}$	4	mW
Reverse Voltage	$V_R \text{ max}$	2	V

<b>Monitor Diode</b>	<b>Symbol</b>	<b>Value</b>	<b>Unit</b>
Reverse Voltage	$V_R$ max	10	V
Forward Current	$I_F$ max	2	mA

<b>PIN Photodiode with Preamplifier</b>	<b>Symbol</b>	<b>Value</b>	<b>Unit</b>
Maximum Voltage	$V_{CC}$ max	6	V
Maximum optical power (average)	$P_{\text{port}}$ max	1	mW

## Characteristics

All optical data refer to the optical port at – 40 to + 85 °C Package-Temperature.

<b>Laser Diode</b>	<b>Symbol</b>	<b>Min</b>	<b>Max</b>	<b>Unit</b>
Optical output power (average)	$P_{\text{opt av}}$	1	–	mW
Optical output power (peak)	$P_{\text{opt peak}}$	2	–	mW
Emission wavelength center of range ( $P_{\text{opt}} = 1$ mW)	$\lambda$	1260	1360	nm
Spectral Width (RMS, $P_{\text{opt}} = 1$ mW)	$\Delta\lambda$	–	5.8	nm
Threshold current	$I_{\text{th}}$	2	45	mA
Forward voltage ( $P_{\text{opt}} = 1$ mW)	$V_F$	–	1.5	V
Radiant power at $I_{\text{th}}$	$P_{\text{th}}$	–	50	μW
Slope efficiency	$S$	35	150	mW/A
Variation of 1st derivative of P/I (0.1 to 2.0 mW)	$dP/dI$	– 30	30	%
Differential series resistance ( $P_{\text{opt}} = 1$ mW)	$r_S$	–	8	Ω
Rise and fall time (10% - 90%)	$t_r, t_f$	–	0.5	ns
Temperature coefficient of wavelength	$TC_\lambda$	–	0.5	nm/K

<b>Monitor-Diode</b>	<b>Symbol</b>	<b>Min</b>	<b>Max</b>	<b>Unit</b>
Dark current, $V_R = 5$ V, $P_{opt} = 0$	$I_R$	–	0.5	$\mu\text{A}$
Photocurrent, $P_{opt} = 1$ mW	$I_P$	100	1000	$\mu\text{A}$
Capacitance, $V_R = 5$ V, $f = 1\text{MHz}$	$C_5$	–	10	$\text{pF}$
Tracking error, $V_R = 5$ V, (see note 1)	$TE$	– 1	1	$\text{dB}$

<b>PIN Photodiode with Preamplifier</b>	<b>Symbol</b>	<b>Min</b>	<b>Max</b>	<b>Unit</b>
Supply Voltage	$V_{CC}$	4.5	5.5	V
Supply Current	$I_{CC}$	–	47	mA
Optical Sensitivity ( $\text{BER} \leq 10^{-10}$ )	$S$	– 28	–	$\text{dBm}$
Linear Bandwidth (– 3 dB)	$BW$	400	–	MHz
Optical Overload (average)	$P_{max}$	– 8	–	$\text{dBm}$
Transimpedance (differential)	$R_T$	80	120	$\text{k}\Omega$
Gain (differential)	$G$	70	175	$\text{mV}/\mu\text{W}$

<b>Module</b>	<b>Symbol</b>	<b>Value</b>	<b>Unit</b>
Optical Crosstalk (see note 2)	$\text{CRT}$	< – 47	dB
Backreflection (Return Loss) @ $\lambda_{in} = 1310$ nm	–	< – 6	dB
Backreflection (Return Loss) @ $\lambda_{in} = 1550$ nm	–	< – 20	dB

Note 1: The tracking error TE is the variation rate of  $P_{opt}$  at constant current  $I_{mon}$  over a specified temperature range and relative to the reference point:  $I_{mon,ref} = I_{mon}(T = 25^\circ\text{C}, P_{opt} = 1 \text{ mW})$ . Thus, TE is given by:

$$TE[\text{dB}] = 10 \times \log \frac{P_{opt}[T_c] - P_{opt}[25^\circ\text{C}]}{P_{opt}[25^\circ\text{C}]}$$

Note 2: Optical Crosstalk is defined as  $CRT = 10 \times \log(P_2/P_1)$  with:  $P_1 = P_{opt} = 1 \text{ mW}$  with no optical input power  $P_{port}$  and  $P_2$  the necessary optical input power  $P_{port}$  at  $\lambda = 1550 \text{ nm}$  to get for  $P_{opt} = 0$  the same receiver signal level as before.

### **Accompanying Information**

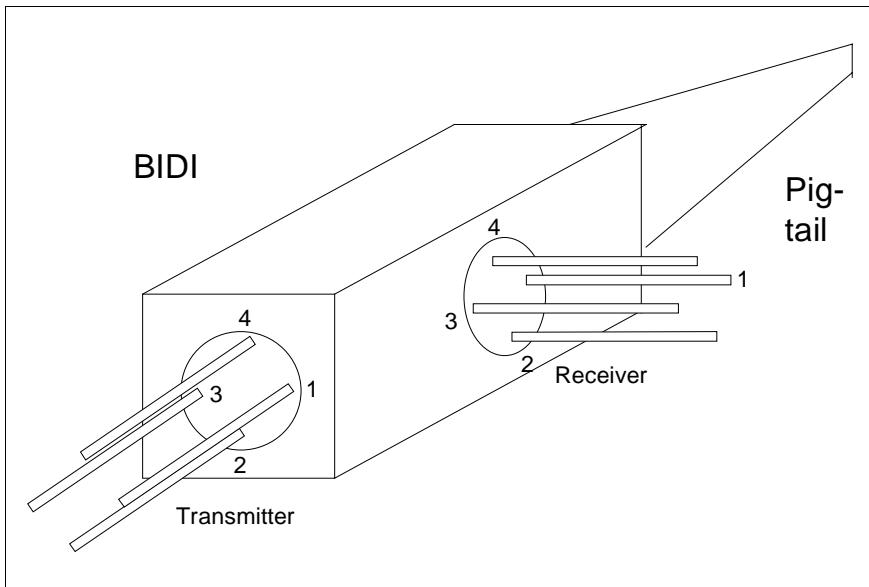
$T = 25 \text{ }^{\circ}\text{C}$ : Threshold current, slope efficiency, monitor current for 1 mW output power, peak wavelength for 1 mW output power.  
 $T = 85 \text{ }^{\circ}\text{C}$ : Threshold current, slope efficiency

### **Pigtail**

<b>Fiber Pigtail, Single Mode, Silica</b>	<b>Min</b>	<b>Max</b>	<b>Unit</b>
Mode field diameter	8	10	$\mu\text{m}$
Cladding diameter	123	127	$\mu\text{m}$
Mode field/cladding concentricity error	–	1	$\mu\text{m}$
Cladding non-circularity	–	2	%
Mode field non-circularity	–	6	%
Cut-off wavelength	1250	–	nm
Jacket diameter	0.8	1.0	mm
Bending radius	30	–	mm
Tensile strength fiber/case	5	–	N
Length	0.8	1.2	m

### **Connector**

all standard connectors like FC/PC, SC, SC APC, available

**Schematic Package Outline and Pinning****Transmitter**

1 LK  
2 Case  
3 MK, LA  
4 MA

**Receiver**

1 Out +  
2 Gnd, Case  
3 Out -  
4 V<sub>CC</sub>